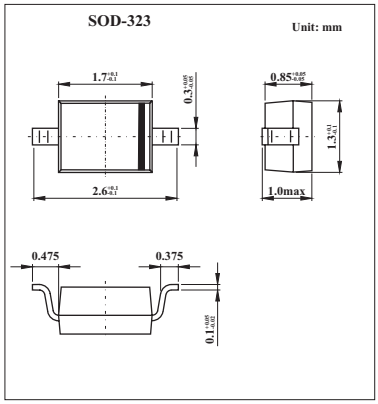
TY Semicondutor®

Product specification

BAR 63-03W



■ Features

- PIN diode for high speed switching of RF signals
- Low forward resistance
- Very low capacitance
- For frequencies up to 3 GHz

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	50	V
Forward current	I_F	100	mA
Total Power dissipation $T_S \leqslant 111℃$	P_{tot}	250	mW
Operating temperature range	T_{op}	-55 to +150	℃
Storage temperature range	T_{stg}	-55 to +150	℃
Junction - soldering point[1)]	R_{thJA}	⩽ 235	K/W
Junction-soldering point	R_{thJS}	⩽ 155	K/W

Note:

1.Package mounted on alumina 15mm x 16.7mm x 0.7mm

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	I_R = 5 μA	50			V
Reverse current	I_R	V_R = 50 V			50	nA
Forward voltage	V_F	I_F = 100 mA		0.95	1.2	V
Diode capacitance	C_T	V_R = 0 V, f = 100 MHz		0.3		pF
		V_R = 5 V, f = 1 MHz		0.21	0.3	
Forward resistance	rf	I_F = 5 mA, f = 100 MHz		1.2	2	Ω
		I_F = 10 mA, f = 100 MHz		1		
Charge carrier life time	τ_{rr}	I_F = 10 mA, I_R = 6 mA,I_R = 3mA		75		ns
Series inductance	Ls			2		nH

■ Marking

Marking	G